



OCTAL BUS TRANSCEIVER WITH BUS HOLD / 3 STATE OUTPUTS

## Description

The 74LVCH245A is an octal transceiver designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable  $(\overline{OE})$  pin can be used to disable the device so the buses effectively are isolated.

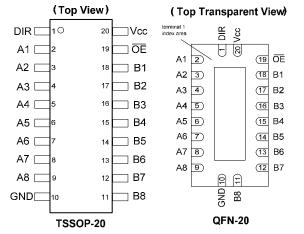
The device is designed for operation with a power supply range of 1.65V to 3.6V.

The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

Bus hold circuitry holds unused or undriven inputs at a high or low logic state. The use of external pull-up or pull down resistors is not recommended.

### Features

- Supply Voltage Range from 1.65V to 3.6V
- Sinks or Sources 24ma at V<sub>CC</sub> = 3V
- CMOS Low Power Consumption
- IOFF Supports Partial Power Down Operation
- Inputs or Outputs Accept Up to 5.5V
- Inputs Can Be Driven by 3.3V or 5V Allowing for Mixed Voltage Applications
- Schmitt Trigger Action at All Inputs
- Typical V<sub>OLP</sub> (Quiet Output Ground Bounce) Less Than 0.8V with V<sub>CC</sub> = 3.3V and T<sub>A</sub> = +25°C
- Typical V<sub>OHV</sub> (Quiet Output dynamic VOH) Greater than 2.0V with  $V_{CC}$  = 3.3V and T<sub>A</sub> = +25°C
- ESD Protection Tested per JESD 22
  - Exceeds 200-V Machine Model (A115)
  - Exceeds 2000-V Human Body Model (A114)
  - Exceeds 1000-V Charged Device Model (C101)
  - Latch-Up Exceeds 250mA per JESD 78, Class I
- All devices are:
  - Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
  - Halogen and Antimony Free. "Green" Device (Note 3)
- Notes:
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
  - 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

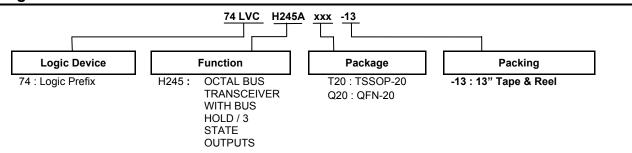


# Applications

- General Purpose Logic
- Bus Driving
- Power Down Signal Isolation
- Wide array of products such as:
  - PCs, Notebooks, Netbooks, Ultrabooks
  - Networking Computer Peripherals, Hard Drives, CD/DVD ROM
  - TV, DVD, DVR, Set Top Box



# **Ordering Information**



Part Number	Package	Package	Package	13" Tape	and Reel
Part Number	Code	(Note 4 & 5)	Size	Quantity	Part Number Suffix
74LVCH245AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65 mm lead pitch	2500/Tape & Reel	-13
74LVCH245AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50 mm lead pitch	2500/Tape & Reel	-13

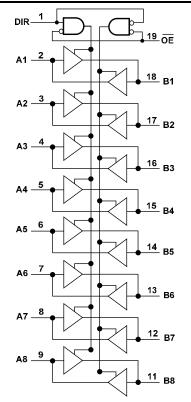
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

## **Pin Descriptions**

Pin	Pin	Description
Number	Name	Description
1	DIR	Direction Control
2	1A1	Data Input
3	2Y4	Data Output
4	1A2	Data Input
5	2Y3	Data Output
6	1A3	Data Input
7	2Y2	Data Output
8	1A4	Data Input
9	2Y1	Data Output
10	GND	Ground
11	2A1	Data Input
12	1Y4	Data Output
13	2A2	Data Input
14	1Y3	Data Output
15	2A3	Data Input
16	1Y2	Data Output
17	2A4	Data Input
18	1Y1	Data Output
19	20E	Output Enable 2
20	Vcc	Supply Voltage

# Logic Diagram



# **Function Table**

INP	UTS	<b>•</b> <i>• •</i>		
ŌE	DIR	Operation		
L	L	B Data to A Bus		
L	Н	A Data to B Bus		
Н	Х	Bus Isolation		



# Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I <sub>IK</sub>	Input Clamp Current VI< 0V	-20	mA
I <sub>OK</sub>	Output Clamp Current V <sub>O</sub> < 0V	-50	mA
lo	Continuous Output Current -0.5V < V <sub>O</sub> V <sub>CC</sub> +0.5V	±50	mA
lcc	Continuous Current Through V <sub>CC</sub>	100	mA
I <sub>GND</sub>	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
P <sub>TOT</sub>	Total Power Dissipation	500	mW

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

# **Recommended Operating Conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
	Operating	1.65	3.6	V	
V <sub>CC</sub>	Supply Voltage	Data Retention Only	1.5	—	V
VI	Input Voltage	—	0	5.5	V
Vo	Output Voltage	—	0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.65V	—	-4	
	High-Level Output Current	V <sub>CC</sub> = 2.3V	—	-8	
lон		V <sub>CC</sub> = 2.7V	—	-12	mA
		V <sub>CC</sub> = 3.0V	—	-24	
		V <sub>CC</sub> = 1.65V	—	4	
		V <sub>CC</sub> = 2.3V	—	8	6
IOL	Low-Level Output Current	V <sub>CC</sub> = 2.7V	—	12	mA
		V <sub>CC</sub> = 3.0V	—	24	
Δt/ΔV	Input Transition Rise or Fall Rate		_	10	ns/V
T <sub>A</sub>	Operating Free-Air Temperature		-40	+125	°C



# **Electrical Characteristics**

Ourseland	Demonster	Toot Conditions		T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	11
Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Max	Min	Max	Unit
			1.65V to 1.95	V <sub>CC</sub> X 0.65		V <sub>CC</sub> X 0.65		
V <sub>IH</sub>	High-Level Input Voltage		2.3V to 2.7V	1.7		1.7		V
	vollage		3.0V to 3.6 V	2		2		
			1.65V to 1.95	_	V <sub>cc</sub> X 0.35	_	V <sub>cc</sub> X 0.35	
VIL	Low-Level input voltage		2.3V to 2.7V	_	0.7	_	0.7	V
	voltage		3.0 V to 3.6V	—	0.8	—	0.8	
		I <sub>он</sub> = -50µА	1.65V to 5.5V	V <sub>CC</sub> -0.2	—	V <sub>CC</sub> -0.3	—	
		I <sub>он</sub> = -4mА	1.65V	1.2	—	1.05	—	
V	High-Level Output	I <sub>он</sub> = -8mA	2.3V	1.7	—	1.65	—	
$V_{OH}$	Voltage	L = 10mA	2.7V	2.2	—	2.05	—	v
		I <sub>он</sub> = -12mA	3.V	2.4	_	2.48	_	v
		I <sub>OH</sub> = -24mA	3.0V	2.3	_	2.0	_	
		I <sub>OL</sub> = 100μA	1.65V to 5.5V	_	0.2	_	0.3	
	Low-Level Output Voltage	I <sub>OL</sub> = 4mA	1.65V	_	0.45	_	0.65	
Vol		I <sub>OL</sub> = 8mA	2.3V	_	0.60	_	0.80	V
		I <sub>OL</sub> = 12mA	2.7V	_	0.40		0.60	
		I <sub>OL</sub> = 24mA	3.V	_	0.55	_	0.80	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 0$ or 5.5V	0V	_	±10	—	±20	μA
I,	Input Current Control Pins	V <sub>I</sub> = GND or 5.5V	0 to 5.5V	_	±5	—	±20	μA
		V <sub>1</sub> = 0.58V	4.0514	25		15		
		V <sub>1</sub> = 1.07	1.65V	-25		-15		
	Input Current	V <sub>1</sub> = 0.7V	0.01/	45		35		
I <sub>I(HOLD)</sub>	Required to Change	V <sub>I</sub> = 1.7V	2.3V	-45		-35		μA
	State	V <sub>1</sub> = 0.8V	0.01/	75	_	60	_	
		V <sub>1</sub> = 2.0V	3.0V	-75	_	-60	_	
		V <sub>I</sub> = 0 or 3.6V	3.6V	_	±500	_	±500	
l <sub>oz</sub>	Z-State current	$V_1 = GND \text{ or } 5.5V$ $V_0 = 0 \text{ or } 5.5V$	3.6V	_	±5	—	± 20	uA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}$ $I_O = 0$	6.0V	_	10	_	40	μA
$\Delta I_{CC}$	Additional Supply Current	One input at V <sub>CC</sub> -0.6V lo = 0A	2.7V to 3.6V	_	500	—	5000	μA
Ci	Input Capacitance	$V_{I}$ = GND or $V_{CC}$	3.3V	4.0 ty	/pical	4.0 ty	/pical	
Co	Output Capacitance	$V_{o}$ = GND or $V_{cc}$	3.3V	5.5 ty	/pical	5.5 typical		pF



# **Switching Characteristics**

Symbol Parameter	Test Conditions	V <sub>cc</sub>	-	Γ <sub>A</sub> = +25°0	•		l0°C to 5°C		0°C to 5°C	Unit			
		Conditions		Min	Ту	Max	Min	Max	Min	Max			
	_		1.8V ± 0.15V	1	6.0	12.2	1	12.7	1	16.9			
	Propagation	Figure 1	2.5V ± 0.2V	1	3.9	8.1	1	8.5	1	9.1			
t <sub>PD</sub>	Delay A <sub>N</sub> to B <sub>N</sub> or B <sub>N</sub> to A <sub>N</sub>	_	2.7V	1	4.2	8.7	1	9.6	1	9.9	ns		
			3.3V ± 0.3V	1.5	3.8	8.1	1.5	8.7	1.5	9.2			
	Enable Time $\overline{OE}$ to $A_N$				1.8V ± 0.15V	1	7	14.8	1	15.3	1	22.5	
				Figure 1	2.5V ± 0.2V	1	4.5	10	1	10.5	1	12.4	
t <sub>EN</sub>		-	2.7V	1	5.4	9.3	1	9.5	1	12.0	ns		
	or $\overline{OE}$ to $B_N$		3.3V ± 0.3V	1.5	4.4	8.3	1.5	8.5	1.5	11.0			
	Disable Time		1.8V ± 0.15V	1	7.8	16.5	1	17	1	18.4			
	$\overline{OE}$ to A <sub>N</sub>	Figure 1	2.5V ± 0.2V	1	4	9	1	9.5	1	10.5			
t <sub>DIS</sub>	$\begin{array}{c c} t_{\text{DIS}} & \text{OE to } A_{\text{N}} \\ \text{or } \overline{\text{OE}} \text{ to } B_{\text{N}} \end{array}$	-	2.7V	1	4.4	8.3	1	8.5	1	10.0	ns		
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0			
t <sub>sk(0)</sub>	Output Skew Time		$3.3V \pm 0.3V$	—	_	1.0	_	—	_	1.5	ns		

# **Operating Characteristics**

T <sub>A</sub> = +25°C					
Symbol	Parameter	<b>Test Conditions</b>	Vcc	Тур	Unit
	Deven die ein etien		1.8V ± 0.15V	9.9	
C <sub>pd</sub>	C <sub>pd</sub> Power dissipation capacitance per gate	F = 10MHz Outputs Enabled	2.5V ± 0.2V	10.2	pF
	capacitance per gate		3.3V ± 0.3V	10.6	

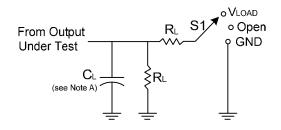
# **Package Characteristics**

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 8)	—	74	—	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 8)	_	15	—	°C/W
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 8)	_	67	_	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 8)	—	20	—	°C/W

Note: 8. Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.

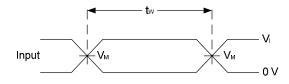


### **Parameter Measurement Information**

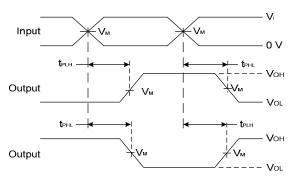


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	VLOAD
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

	In	puts	N.			_	
V <sub>cc</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub> V <sub>LOAD</sub>		C∟	RL	VA
1.8V ± 0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	30pF	1KΩ	0.15V
2.5V ± 0.2V	Vcc	≤2ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30pF	500Ω	0.15V
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V
3.3V ± 0.3V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V



#### Voltage Waveform Pulse Duration

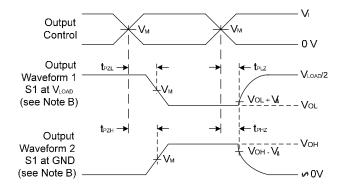




- Notes: A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz. C. Inputs are measured separately one transition per measurement. D. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis.</sub> E. t<sub>PZL</sub> and t<sub>PZH</sub> are the same as t<sub>EN0</sub>

  - F.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD.}}$

Figure 1 Load Circuit and Voltage Waveforms

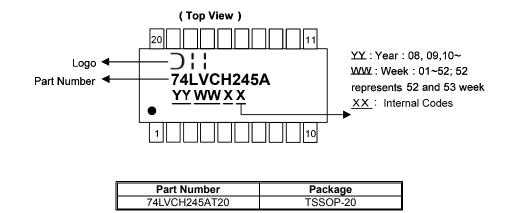


Voltage Waveform Enable and Disable Times Low and High Level Enabling

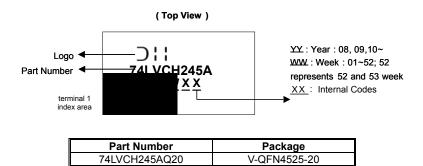


### **Marking Information**

### (1) TSSOP20



#### (2) QFN-20 (V-QFN4525-20)

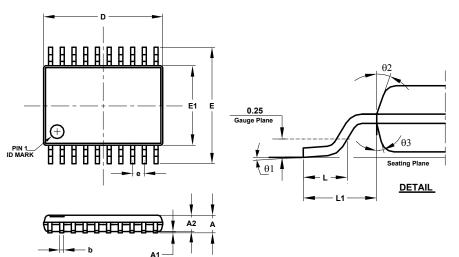




# Package Outline Dimensions (All Dimensions in mm)

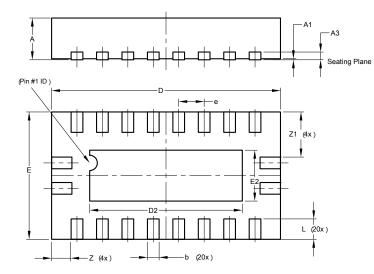
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) TSSOP-20



	TSSO	P-20					
Dim	Min Max Typ						
Α	-	1.20	-				
A1	0.05	0.15	-				
A2	0.80	1.05	-				
b	0.19	0.30	-				
С	0.09	0.20	-				
D	6.40	6.60	6.50				
Е	6.20	6.60	6.40				
E1	4.30	4.50	4.40				
e	0	.65 BSC	)				
L	0.45	0.75	0.60				
L1		1.0 REF					
θ1	0°	8°	-				
θ2	10°	14°	12°				
θ3	10°	14°	12°				
All I	Dimensi	ons in r	nm				

#### (2) QFN-20 (V-QFN4525-20)



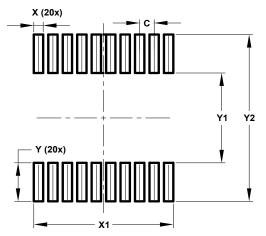
V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
E	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
L	0.30	0.50	0.40	
Z	-	-	0.385	
Z1	-	-	0.885	
All Dimensions in mm				



# Suggested Pad Layout

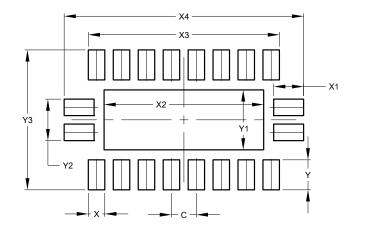
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### (1) TSSOP-20



Dimensions	Value (in mm)	
С	0.650	
Х	0.420	
X1	6.270	
Y	1.789	
Y1	4.160	
Y2	7.720	

#### (2) QFN-20 (V-QFN4525-20)



Dimensions	Value (in mm)
С	0.500
Х	0.330
X1	0.600
X2	3.200
X3	3.830
X4	4.800
Y	0.600
Y1	1.200
Y2	0.830
Y3	2.800



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